

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A process for forming a resist pattern, which increases the amount of reduction in thickness of a chemically amplified positive photoresist coating after development by 100 Å to 600 Å in comparison with the case of not applying the composition for preventing development-defects, comprising: a step of forming a chemically amplified positive photoresist coating on a substrate having a diameter of 8 inches or more by application; a step of applying a composition for preventing development-defects containing a surfactant on the chemically amplified positive photoresist coating; a step of baking after at least either the step of forming the chemically amplified positive photoresist coating by application or the step of applying the composition for preventing development-defects; a step of selectively exposing the chemically amplified positive photoresist coating; a step of post-exposure baking the chemically amplified positive photoresist coating; and a step of developing the chemically amplified positive photoresist coating,

wherein said surfactant is at least one member selected from the group consisting of (1) ~~an ammonium salt, a tetraalkylammonium salt or a C₄ to C₄ alkanolamine salt of C₄ to C₁₅ perfluoroalkylcarboxylic acid~~ [[.]] and (2) ~~an ammonium salt, a tetraalkylammonium salt or a C₄ to C₄ alkanolamine salt of C₄ to C₁₀ perfluoroalkylsulfonic acid, (3) a quaternary ammonium salt of perfluoroadipic acid, and (4) a fluorinated alkyl quaternary ammonium salt of inorganic acid which is at least one member selected from the group consisting of sulfuric acid, hydrochloric acid, nitric acid and hydroiodic acid,~~ at the same time said surfactant being one that is formed at the equivalent ratio of acid to base of 1:1.04 – 1:3.

2. (currently amended) A composition for preventing development-defects which contains a surfactant and is used for the process of forming a resist pattern that increases

the amount of reduction in thickness of a chemically amplified positive photoresist coating after development by 100 Å to 600 Å in comparison with the case of not applying the composition for preventing development-defects, comprising: a step of forming a chemically amplified positive photoresist coating on a substrate having a diameter of 8 inches or more by application; a step of applying a composition for preventing development-defects containing a surfactant on the chemically amplified positive photoresist coating; a step of baking after at least either the step of forming the chemically amplified positive photoresist coating by application or the step of applying the composition for preventing development-defects; a step of selectively exposing the chemically amplified positive photoresist coating; a step of post-exposure baking the chemically amplified positive photoresist coating; and a step of developing the chemically amplified positive photoresist coating,

wherein said surfactant is at least one member selected from the group consisting of (1) an ~~ammonium salt~~, a tetraalkylammonium salt ~~or a C₄ to C₄ alkanolamine salt~~ of C₄ to C₁₅ perfluoroalkylcarboxylic acid ~~[[.]]~~ and (2) ~~an ammonium salt~~, a tetraalkylammonium salt ~~or a C₄ to C₄ alkanolamine salt~~ of C₄ to C₁₀ perfluoroalkylsulfonic acid, (3) ~~a quaternary ammonium salt of perfluoroadipic acid~~, and (4) ~~a fluorinated alkyl quaternary ammonium salt of inorganic acid which is at least one member selected from the group consisting of sulfuric acid, hydrochloric acid, nitric acid and hydroiodic acid~~, at the same time said surfactant being one that is formed at the equivalent ratio of acid to base of 1:1.04 – 1:3.